# aAs Wafers



## cifications

| | |
|---|---|
| Diameter, mm | 100 |
| Thickness, µm | 450; 625 |
| Deviation from nominal value, µm | ± 25 |
| ystallographic orientation, ° | (100); (100)+10°; (111) A |
| Conductivity type | N |
| Flat orientation | SEMI EJ |
| olishing | ouble-sided |
| pant | Si |
| harge carrier mobility, $cm^2/V{\cdot}sec$ | > 1200 |
| harge carrier concentration, cm-3 | From $1{\cdot}10^{17}$ to $3{\cdot}10^{18}$ |
| Dislocation density, cm-2 | < 500 |
| TTV minimum, µm | 2 |
| TTV minimum/standard, µm | p to 5 |